

Quasi Phase Matched Gallium Arsenide for Mid-Infrared Applications

E. Lallier¹, D. Faye¹, A. Grisard¹, B. Gérard²

¹Thales Research & Technology, RD 128, 91767 Palaiseau, France

²Alcatel-Thales III-V Lab, RD 128, 91767 Palaiseau, France

e-mail: eric.lallier@thalesgroup.com

Summary

Powerful coherent laser sources are needed throughout the mid-infrared region for a number of civilian or defense applications, exploiting either the atmospheric transmission windows, or the fingerprint of common molecules. Nonlinear optical materials play a key role as they permit the frequency down-conversion of mature near-infrared solid-state lasers into the mid-IR, where few direct laser solutions exist.

Gallium arsenide (GaAs) has excellent characteristics for parametric frequency conversion and is potentially one of the most attractive mid-IR nonlinear-optical materials. It has an extremely large second-order nonlinear optical coefficient $d_{14} \gg 100$ pm/V, wide transparency range 1-16 μm , excellent mechanical properties and high thermal conductivity. The crystal is optically isotropic precluding birefringent phasematching, however with appropriate quasi-phasematching (QPM) means, it can be used for numerous nonlinear optical applications.

The drawbacks of previous QPM GaAs devices based on diffusion bonding of thin GaAs wafers with periodic orientations have been eliminated by the use of waferscale processing techniques for fabricating periodically-inverted (orientationpatterned) structures in GaAs and Hydride Vapour Phase Epitaxy (HVPE) thick-film regrowth [1,2]. HVPE allows growth rates of about 30 $\mu\text{m}/\text{h}$ resulting in low doped layers with excellent optical properties. Careful growth parameters selection can preserve the periodic orientation of the template substrate to thicknesses in excess of 500 μm , thus enabling free space propagation of pump and signal beams. After a brief review of past QPM GaAs research and achievements, this paper will focus on recent results obtained with thick OP-GaAs structures. Reproducible growth of 500 μm thick and

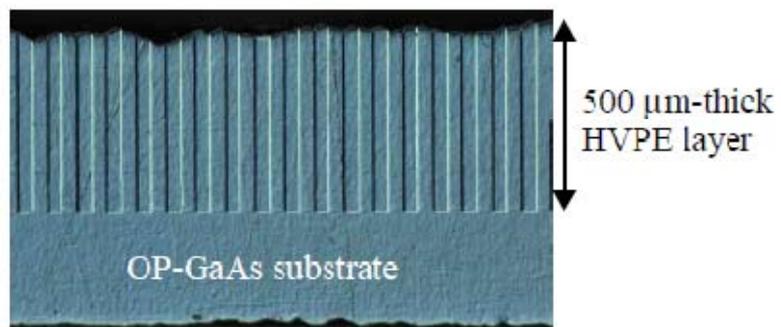


Figure 1: Cross-section of a 500- μm -thick GaAs film grown over a 60 μm period OP-GaAs template.

3 cm long samples with optical losses down to 0.01 cm^{-1} has enabled the demonstration of high average power pulsed mid-IR OPOs and may soon permit the realization of a CW-pumped devices with large tunability [3,4].

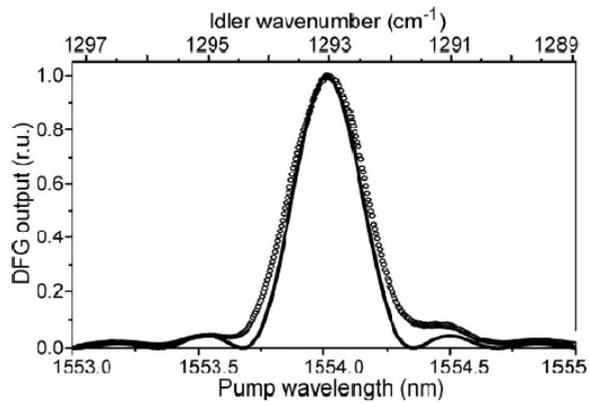


Figure 2.:Difference frequency generation around 8 μm using Er (1.5 μm) and Tm (1.9 μm) CW fiber laser sources. The measured phase-matching curve is very close to the theoretical expected one and demonstrates the high quality of the 33 mm long OP-GaAs sample (after ref. 4).

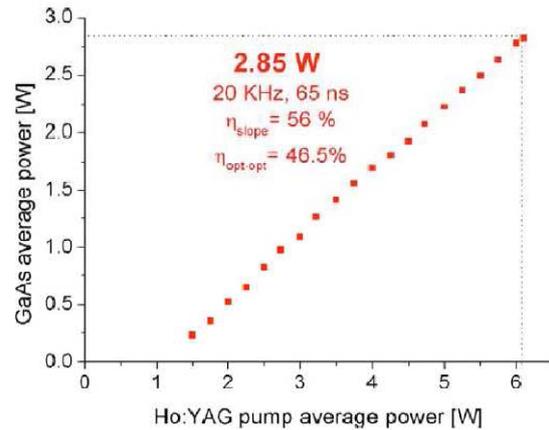


Figure 3 : Output power in the 3-5 μm range of an OP-GaAs OPO pumped by a 2.1 μm 20 kHz Ho :YAG laser (after ref. 3).

References

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